



DMP4013SPS

P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
-40V	15mΩ @ V_{GS} = -10V	-61A
	$23m\Omega @ V_{GS} = -4.5V$	-49A

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Reverse Polarity Protection
- BLDC Motor Control
- Power Management Functions

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMP4013SPSQ</u>)

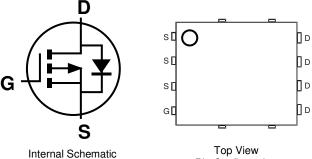
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208⁽³⁾
- Weight: 0.097 grams (Approximate)



Top View

Bottom View



Pin Configuration

Ordering Information (Note 4)

Case	Packaging
PowerDI5060-8	2,500 / Tape & Reel

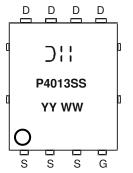
Pin1

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



>;; = Manufacturer's Marking P4013SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-40	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current V_{GS} = -10V (Note 7)	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	-61 -49	A
Continuous Drain Current V_{GS} = -10V (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-11 -9	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-244	A		
Maximum Body Diode Continuous Current (Note 7)			Is	-61	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-244	A
Avalanche Current (Note 8) L = 1mH			I _{AS}	-16	A
Avalanche Energy (Note 8) L = 1mH			E _{AS}	176	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	96	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	44	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{eJC}	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

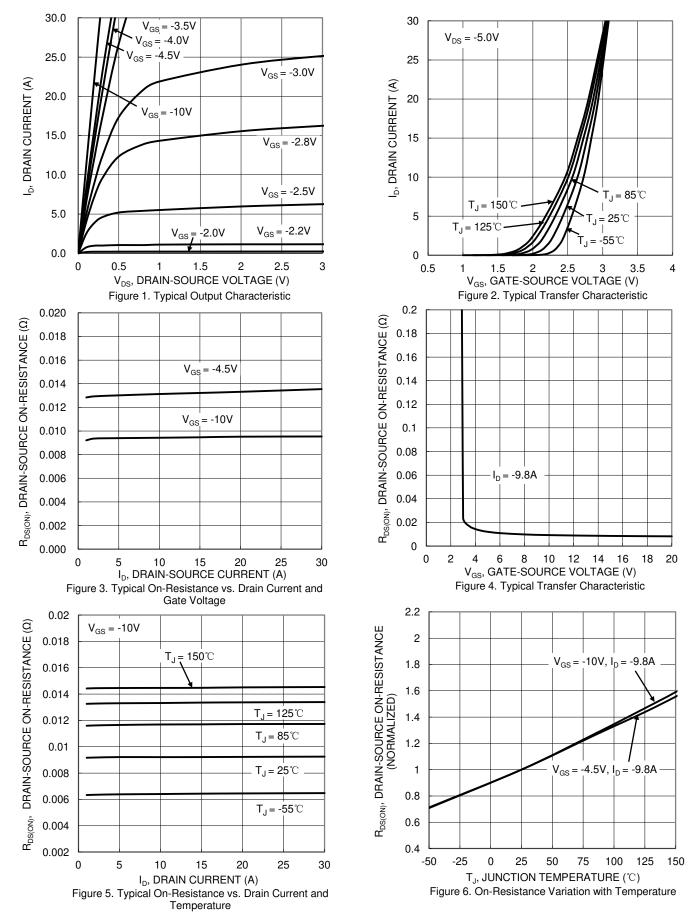
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)						L	
Drain-Source Breakdown Voltage	BV _{DSS}	-40			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_		-1	μA	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
Static Drain-Source On-Besistance	Deserve		9.6	15	mΩ	$V_{GS} = -10V, I_D = -10A$	
	R _{DS(ON)}		13.4	23	1115.2	$V_{GS} = -4.5V, I_D = -8A$	
Diode Forward Voltage	V _{SD}		-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	4004	—		$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		309		pF		
Reverse Transfer Capacitance	Crss		229	_			
Gate Resistance	Rg		3.5		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg		31	_			
Total Gate Charge (V _{GS} = -10V)	Qg	_	67	_	nC	$V_{DS} = -20V,$ $I_D = -10A$	
Gate-Source Charge	Qgs		13.2		nc		
Gate-Drain Charge	Q _{gd}	_	11	_			
Turn-On Delay Time	t _{D(ON)}		9.9			V_{GS} = -10V, V_{DD} = -20V, R_G = 3 Ω , I_D = -10A	
Turn-On Rise Time	t _R	_	32	_			
Turn-Off Delay Time	t _{D(OFF)}	_	46	_	ns		
Turn-Off Fall Time	t _F		53	_]		
Reverse Recovery Time	t _{RR}		19.5	—	ns	I _F = -10A, di/dt = -100A/μs	
Reverse Recovery Charge	Q _{RR}		11.6		nC	I _F = -10A, di/dt = -100A/μs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

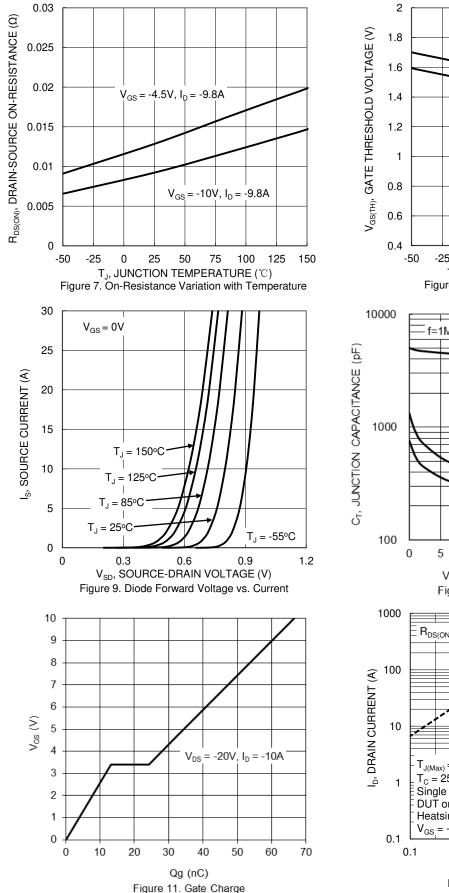
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).

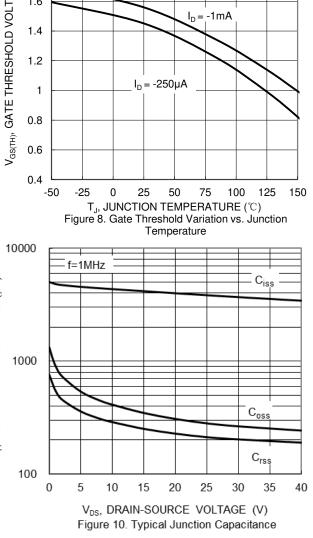
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$. 9. Short duration pulse test used to minimize self-heating effect. 10. Guaranteed by design. Not subject to product testing.

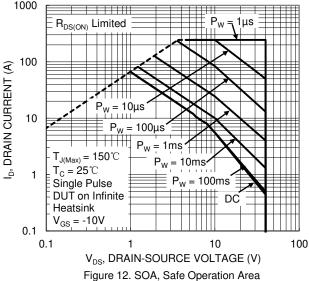






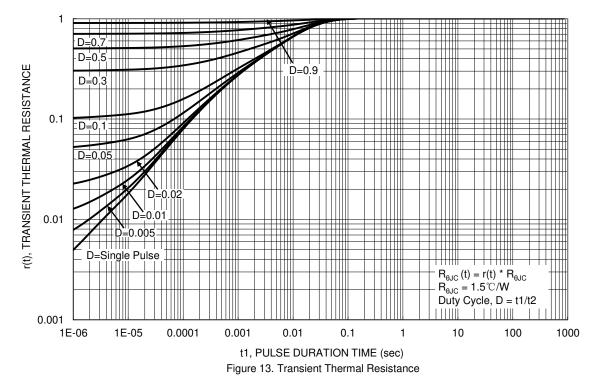






DMP4013SPS Document number: DS41698 Rev. 2 - 2



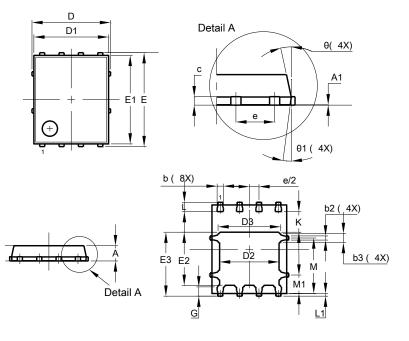




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

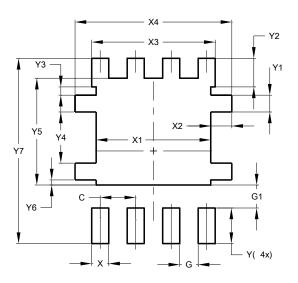


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
E		6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
К	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
Al	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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